

Abstract of the Disclosure

A method of fabricating a semiconductor device is provided. The method includes forming an interconnection line over a substrate. The interconnection line functions as a first electrode. A first insulating layer is formed on the substrate including the metal interconnection line. An electrode layer and an oxide layer are formed on the first insulating layer. A photoresist pattern is formed on the oxide layer. The oxide layer and the electrode layer are etched using the photoresist pattern as an etching mask. As a result, a second electrode and an oxide layer pattern, which are stacked, are formed over the interconnection line. At least the electrode layer is etched using a wet etching technique. The photoresist pattern is then removed.